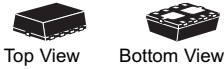




CTLT5551-M832D

**SURFACE MOUNT  
DUAL, HIGH VOLTAGE  
GENERAL PURPOSE  
NPN TRANSISTOR**



**TLM832D CASE**

**MARKING CODE: CFS**

**APPLICATIONS**

General purpose high voltage amplifier applications.

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Collector Current	
Power Dissipation*	
Operating and Storage Junction Temperature	
Thermal Resistance	

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:** The CENTRAL SEMICONDUCTOR CTLT5551-M832D is a Dual NPN General Purpose, High Voltage Amplifier Transistor packaged in the small, thermally efficient, 3x2mm Tiny Leadless Module (TLM<sup>TM</sup>) surface mount case. These devices are designed for applications where small size, operational efficiency, and low energy consumption are the prime requirements.

- Device is **Halogen Free** by design

**FEATURES**

- Dual High Voltage Transistors ( $V_{CBO}=180\text{V Max}$ )
- Low Leakage Current ( $I_{CBO}=50\text{nA Max @ } V_{CB}=120\text{V}$ )
- Low  $V_{CE(SAT)}$  (0.2V Max @  $I_C=50\text{mA}$ )
- Small TLM 3x2mm Leadless Surface Mount Package

SYMBOL		UNITS
$V_{CBO}$	180	V
$V_{CEO}$	160	V
$V_{EBO}$	6.0	V
$I_C$	600	mA
$P_D$	1.65	W
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\Theta_{JA}$	76	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=120\text{V}$		50	nA
$I_{CBO}$	$V_{CB}=120\text{V}, T_A=100^\circ\text{C}$		50	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=4.0\text{V}$		50	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	180		V
$BV_{CEO}$	$I_C=1.0\text{mA}$	160		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.20	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.00	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	80		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	80	250	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	30		
$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	MHz

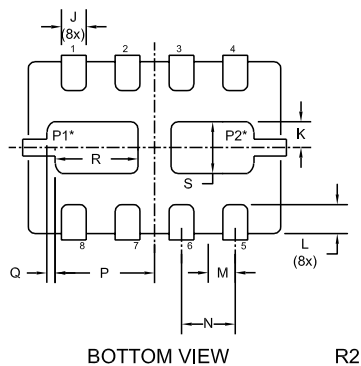
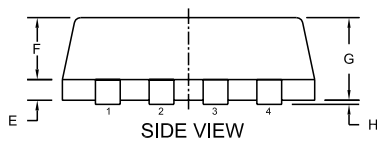
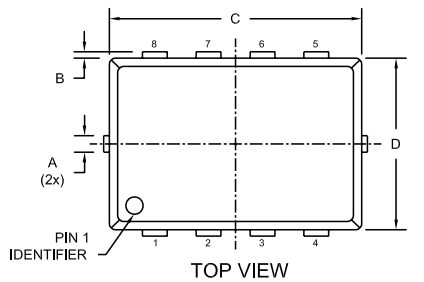
\*FR-4 Epoxy PCB with copper mounting pad area of 54mm<sup>2</sup>

**SURFACE MOUNT  
DUAL, HIGH VOLTAGE  
GENERAL PURPOSE  
NPN TRANSISTOR**

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:**

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0MHz$		6.0	pF
$C_{ib}$	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		20	pF
$h_{fe}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	200	
NF	$V_{CE}=5.0V, I_C=200\mu A, R_S=10\Omega$ $f=10Hz$ to $15.7kHz$		8.0	dB

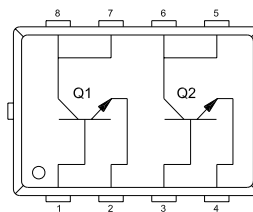
**TLM832D CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS		DIMENSIONS	
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.007	0.012	0.170	0.300
B	-	0.005	-	0.125
C	0.114	0.122	2.900	3.100
D	0.075	0.083	1.900	2.100
E	0.006	0.010	0.150	0.250
F	0.026	0.030	0.650	0.750
G	0.031	0.039	0.800	1.000
H	0.000	0.002	0.000	0.050
J	0.009	0.013	0.240	0.340
K	0.006	0.014	0.160	0.360
L	0.008	0.018	0.200	0.450
M	0.013		0.325	
N	0.026		0.650	
P	0.040	0.048	1.010	1.210
Q	0.004		0.100	
R	0.032	0.040	0.820	1.020
S	0.017	0.025	0.430	0.630

TLM832D (REV: R2)

**PIN CONFIGURATION**



**LEAD CODE:**

- 1) BASE Q1
- 2) EMITTER Q1
- 3) BASE Q2
- 4) EMITTER Q2
- 5) COLLECTOR Q2
- 6) COLLECTOR Q2
- 7) COLLECTOR Q1
- 8) COLLECTOR Q1

**MARKING CODE: CFS**

**\* Note:**

- Exposed pad P1 common to pins 7 and 8
- Exposed pad P2 common to pins 5 and 6

R1 (14-August 2008)